

Abstract of the Disclosure

A semiconductor integrated circuit device includes an internal circuit,
5 a second internal circuit, and an interface circuit. The first internal circuit
includes a first MOS transistor operating with a first voltage higher than a
power supply voltage and having a relatively thick gate insulation layer. The
second internal circuit includes a second MOS transistor operating with a
10 second voltage lower than the first voltage and having a relatively thin gate
insulation layer. The interface circuit restricts a voltage transferred from the
first internal circuit to the second internal circuit so as to reduce an electric
field applied to the gate insulation layer of the second MOS transistor. Thus,
it is possible to prevent a gate insulation layer from being broken by a high
voltage and to prevent the reduction in turn-on speed of the MOS transistor.